

FIG.1

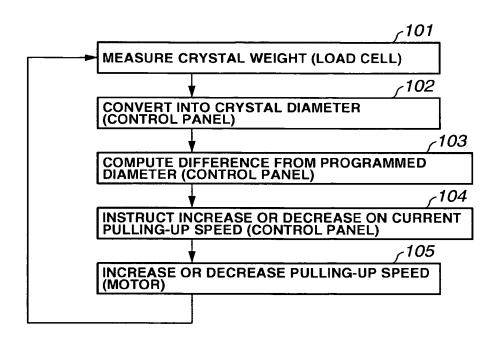


FIG.2

WIDTH OF SPEED FLUCTUATION IN EVERY 10 SEC ΔV (mm/min)	VARIATION IN IMPURITY CONCENTRATION (STRIATION)
0.011	NOT CAUSED
0.015	NOT CAUSED
0.020	NOT CAUSED
0.025	CAUSED
0.030	CAUSED
0.033	CAUSED

FIG.3

Title: METHOD FOR MANUFACTURING SINGLE CRYSTAL SEMICONDUCTOR (Hiroshi INAGAKI et al.) Filed: 8/16/06
Attorney Docket No.: 1110/98029 (SHEET 3 OF 4)

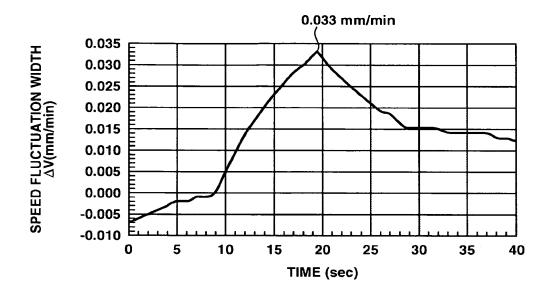


FIG.4

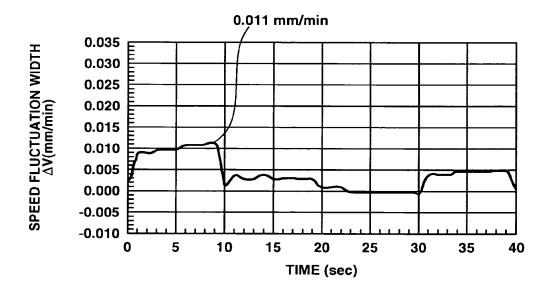


FIG.5

Title: METHOD FOR MANUFACTURING SINGLE CRYSTAL SEMICONDUCTOR (Hiroshi INAGAKI et al.) Filed: 8/16/06
Attorney Docket No.: 1110/98029 (SHEET 4 OF 4)

X-RAY PHOTOGRAPH OF CRYSTAL SECTION

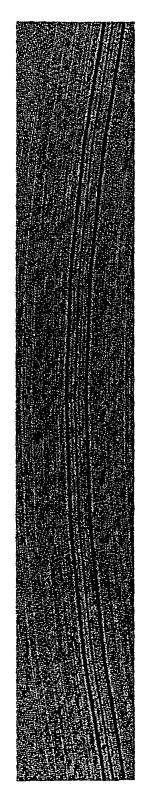


FIG.6A INTERVALS BETWEEN STRIATIONS ARE NON-UNIFORM AND THE STRIATIONS ARE THICK.

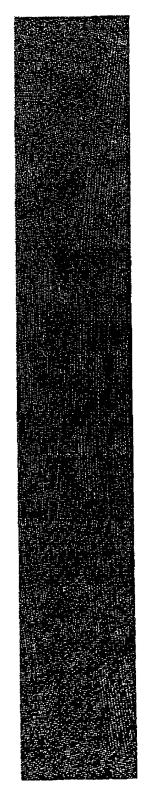


FIG.6B INTERVALS BETWEEN STRIATIONS ARE EQUAL AND THE STRIATIONS ARE DENSE AND THIN.

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